



SSC80A3GT8

P-Channel Enhancement Mode MOSFET

Features

V _{DS}	V _{GS}	R _{DS(ON)}	I _D
-100V	±20V	35mΩ@-10V	-35A
		40mΩ@-4V5	

Description

This device is P-Channel enhancement MOSFET. Uses advanced trench technology and design to provide excellent RDSON with low gate charge. This device is suitable for use in DC-DC conversion, power switch and charging circuit.

100% UIS + ΔVDS + Rg Tested!

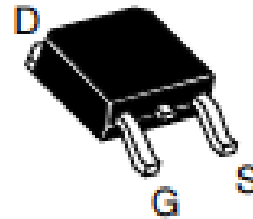
Applications

- Motor Drive Control
- Portable Devices
- DCDC Conversion
- Power Supplies
- Synchronous Rectification

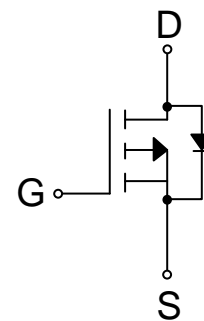
Ordering Information

Device	Package	Shipping
SSC80A3GT8	TO-252-2L	2500/Reel

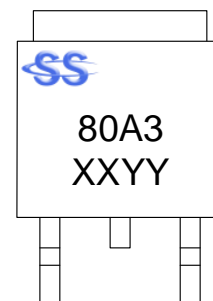
Pin Configuration



TO-252-2L (Top View)



Pin Configuration



Marking

(XXYY: Internal Traceability Code)



➤ **Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise noted)**

Symbol	Parameter	Ratings	Unit
V_{DSS}	Drain-to-Source Voltage	-100	V
V_{GSS}	Gate-to-Source Voltage	± 20	V
I_D	Continuous Drain Current ^d	$T_C=25^\circ\text{C}$	-35
		$T_C=100^\circ\text{C}$	-18
I_{DSM}	Continuous Drain Current ^a	$T_A=25^\circ\text{C}$	-7.5
		$T_A=70^\circ\text{C}$	-5.1
I_{DM}	Pulsed Drain Current ^b	-140	A
P_D	Power Dissipation ^c	$T_C=25^\circ\text{C}$	65
		$T_C=100^\circ\text{C}$	26
P_{DSM}	Power Dissipation ^a	$T_A=25^\circ\text{C}$	3
		$T_A=70^\circ\text{C}$	2
I_{AS}	Avalanche Current ^b L=0.5mH Single Pulse	35	A
E_{AS}	Avalanche Energy ^b L=0.5mH Single Pulse	306	mJ
T_J	Operation junction temperature	-55~150	°C
T_{STG}	Storage temperature range	-55~150	

➤ **Thermal Resistance Ratings ($T_A=25^\circ\text{C}$ unless otherwise noted)**

Symbol	Parameter	Ratings	Unit
$R_{\theta JA}$	Junction-to-Ambient Thermal Resistance ^a	40	°C/W
$R_{\theta JC}$	Junction-to-Case Thermal Resistance	1.9	

Note:

- The value of $R_{\theta JA}$ is measured with the device mounted on 1 in² FR-4 board with 2oz.copper, in a still air environment with $T_A=25^\circ\text{C}$. The value in any given application depends on the user is specific board design. The power dissipation is based on the $t \leq 10\text{s}$ thermal resistance rating.
- Repetitive rating, pulse width limited by junction temperature.
- The power dissipation P_D is based on $T_{J(MAX)}=150^\circ\text{C}$, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heat sinking is used.
- The maximum current rating is package limited.

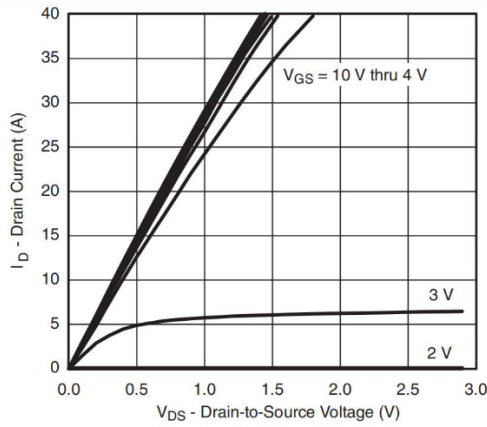


➤ **Electrical Characteristics (T_A=25°C unless otherwise noted)**

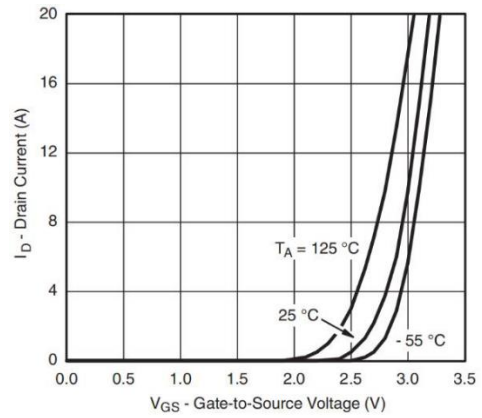
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = -250μA	-100			V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250μA	-1.0	-2.0	-3.0	V
Drain-Source On-Resistance	R _{DS(on)}	V _{GS} = -10V, I _D = -15A		35	51	mΩ
		V _{GS} = -4.5V, I _D = -10A		40	68	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = -100V, V _{GS} = 0V			-1	μA
Gate-Source Leak Current	I _{GSS}	V _{GS} = ±20V, V _{DS} = 0V			±100	nA
Forward Voltage	V _{SD}	V _{GS} = 0V, I _S = -10A		-0.8	-1.4	V
Gate Resistance	R _G	V _{DS} = 0V, f = 1MHz		12.5		Ω
Input Capacitance	C _{ISS}	V _{DS} = -50V, V _{GS} = 0V, f = 1MHz		4560		pF
Output Capacitance	C _{OSS}			229		
Reverse Transfer Capacitance	C _{RSS}			140		
Total Gate Charge	Q _G	V _{GS} = -10V, V _{DS} = -50V, I _D = -15A		77		nC
Gate to Source Charge	Q _{GS}			22		
Gate to Drain Charge	Q _{GD}			14		
Turn-on Delay Time	T _{D(ON)}	V _{GS} = -10V, V _{DS} = -50V, R _L = 3.3Ω, R _G = 9.1Ω		11		ns
Rise Time	T _r			43		
Turn-off Delay Time	T _{D(OFF)}			251		
Fall Time	T _f			88		
Diode Recovery Time	T _{rr}	I _F = -20A, di/dt = 100A/us		35		ns
Diode Recovery Charge	Q _{rr}	I _F = -20A, di/dt = 100A/us		52		nC



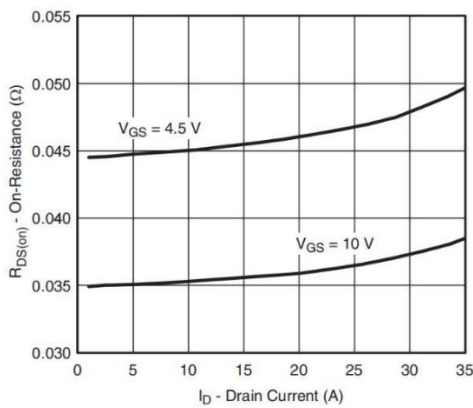
➤ **Typical Performance Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)**



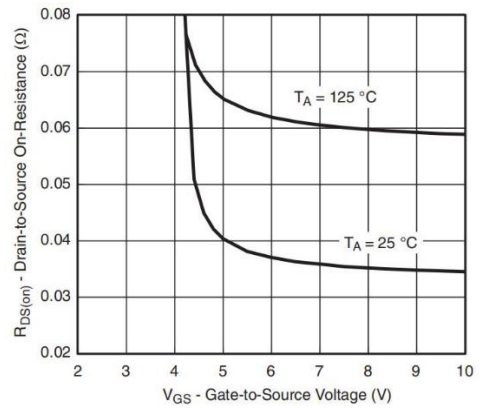
Output Characteristics



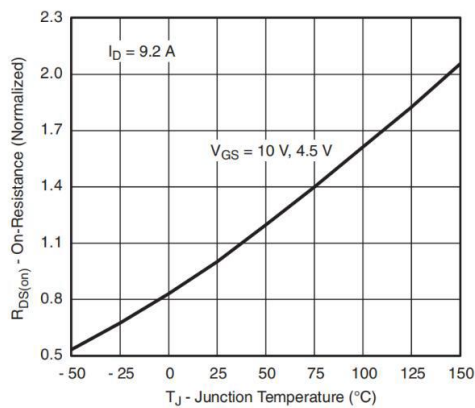
Transfer Characteristics



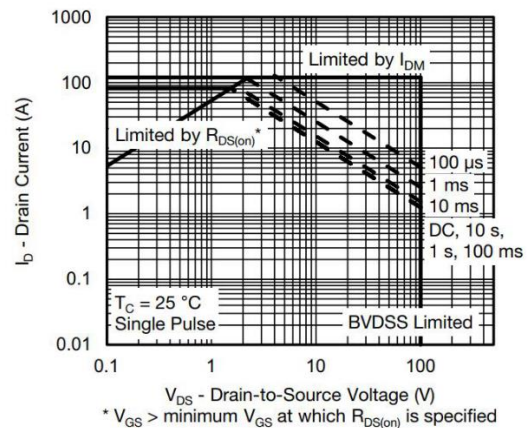
On-Resistance vs. Drain Current and Gate Voltage



On-Resistance vs. Gate-to-Source Voltage



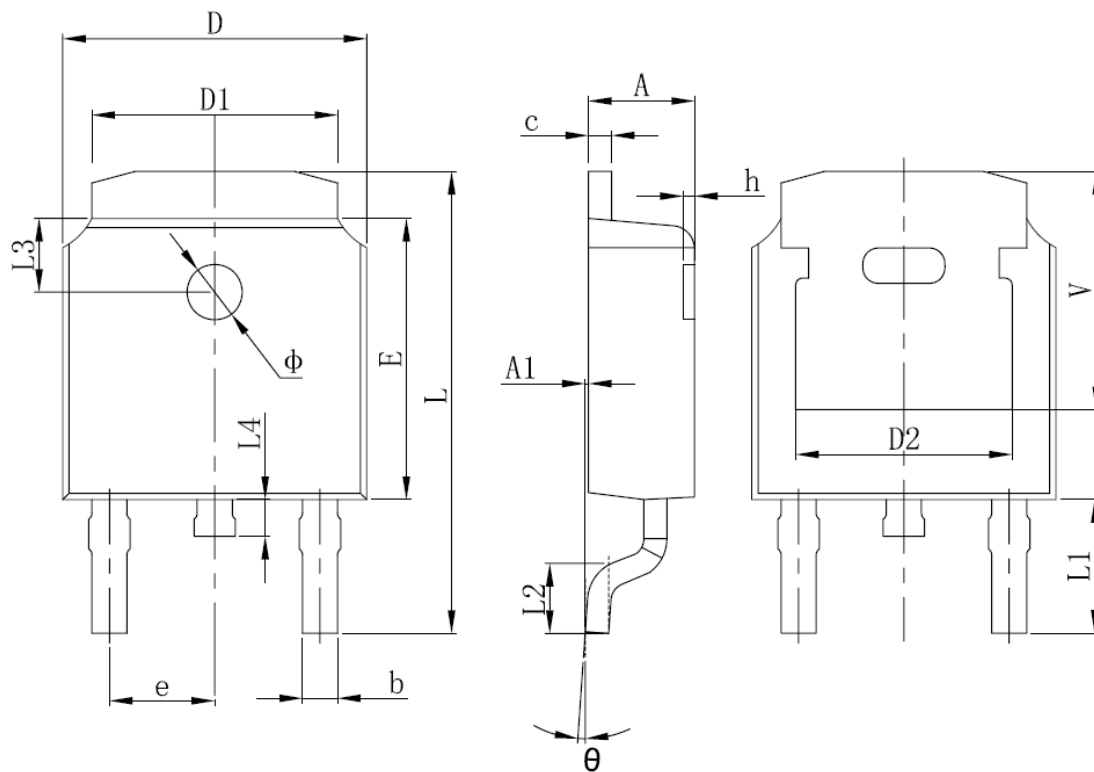
On-Resistance vs. Junction Temperature



Safe Operating Area



➤ Package Information



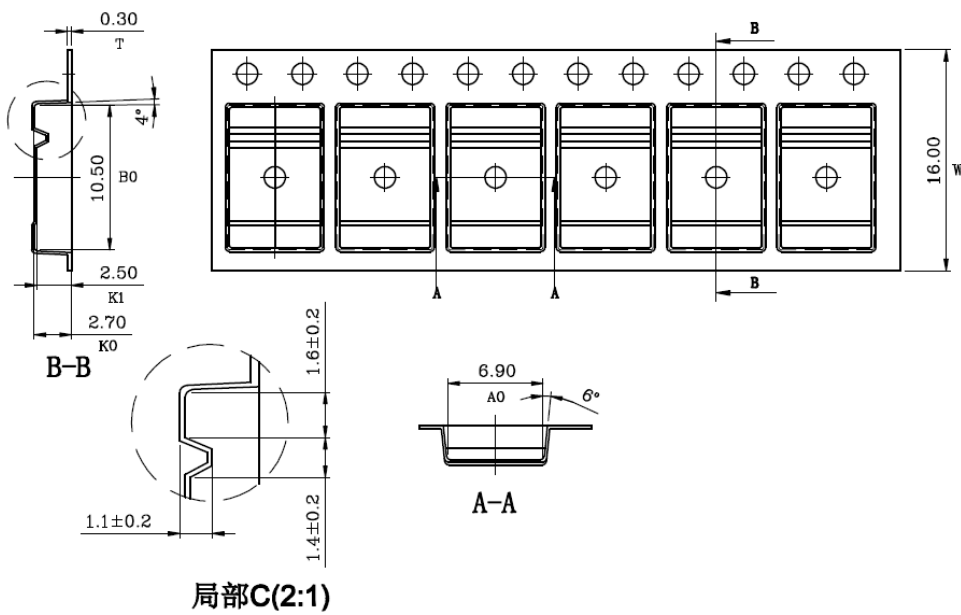
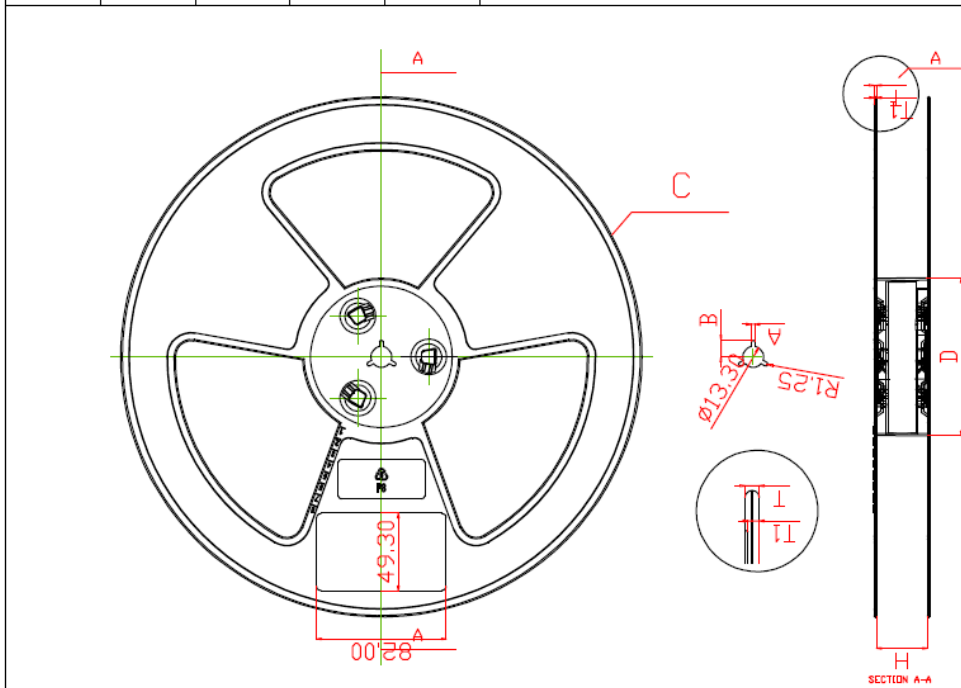
Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.635	0.770	0.025	0.030
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 REF.		0.190 REF.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.712	10.312	0.382	0.406
L1	2.900 REF.		0.114 REF.	
L2	1.400	1.700	0.055	0.067
L3	1.600 REF.		0.063 REF.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.250 REF.		0.207 REF.	



➤ Tape and Reel

材质: PS 未标注公差: ± 0.2

H	12	16	24	32
C ± 0.2	330	330	330	330
T1 ± 0.2	1.45	1.45	1.45	1.45
B ± 0.2	10.7	10.7	10.7	10.7
A ± 0.2	2.5	2.5	2.5	2.5
T ± 0.2	1.85	1.85	1.85	1.85
D ± 0.2	100	100	100	100





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